CY62147V MoBL™
CY62147V18 MoBL2™

256K x 16 Static RAM

Features

- **Low voltage range:**
  - **CY62147V: 1.65V–1.95V**
  - **CY62147V18: 2.7V–3.6V**
- **Ultra-low active, standby power**
- **Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ features**
- **TTL-compatible inputs and outputs**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**

Functional Description

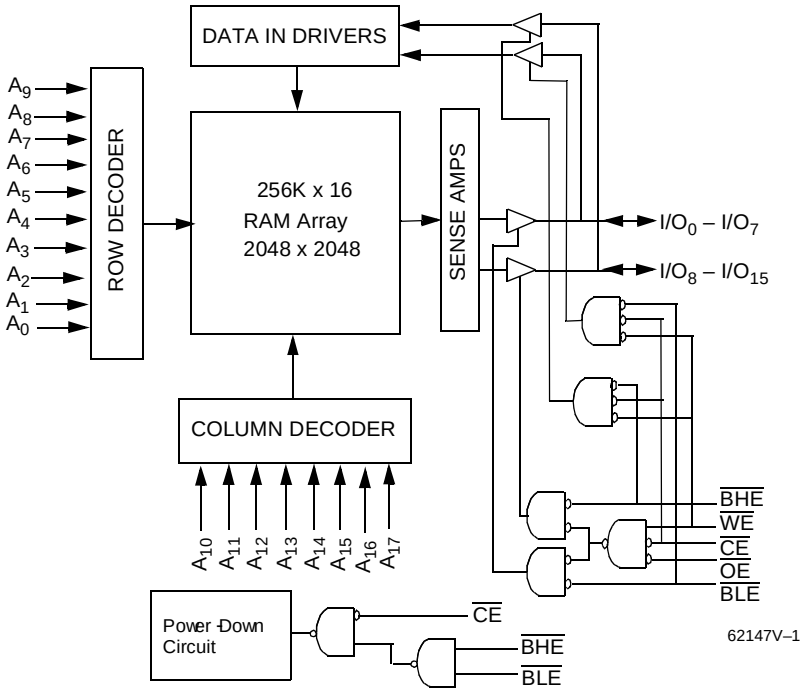
The CY62147V and CY62147V18 are high-performance CMOS static RAMs organized as 262,144 words by 16 bits. These devices feature advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL™) in portable applications such as cellular telephones. The devices also have an automatic power-down feature that significantly reduces power consumption by 99% when addresses are not toggling. The device can also be put into standby mode when deselected ($\overline{CE}$ HIGH) or when $\overline{CE}$ is LOW and both $\overline{BLE}$ and $\overline{BHE}$ are HIGH. The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when: deselected ($\overline{CE}$ HIGH), outputs are disabled ($\overline{OE}$ HIGH), $\overline{BHE}$ and $\overline{BLE}$ are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH), or during a write operation ($\overline{CE}$ LOW, and $\overline{WE}$ LOW).

Writing to the device is accomplished by taking Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{17}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{17}).

Reading from the device is accomplished by taking Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. See the truth table at the back of this data sheet for a complete description of read and write modes.

The CY62147V and CY62147V18 are available in 48-ball FBGA and standard 44-pin TSOP Type II (forward pinout) packaging.

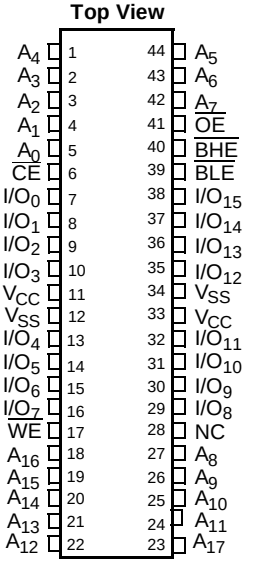
Logic Block Diagram



Pin Configurations

TSOP II (Forward)

Top View



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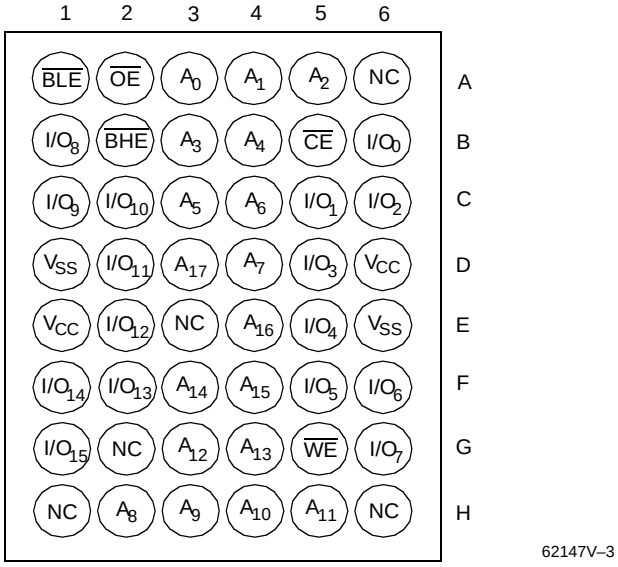
Pin Configuration (continued)

FBGA

Top View



62147V–3

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... –65°C to +150°C

Ambient Temperature with Power Applied ..... –55°C to +125°C

Supply Voltage to Ground Potential ..... –0.5V to +4.6V

DC Voltage Applied to Outputs in High Z State[1] ..... –0.5V to V_{CC} + 0.5V

DC Input Voltage[1] ..... –0.5V to V_{CC} + 0.5V

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... >2001V (per MIL-STD-883, Method 3015)

Latch-Up Current ..... >200 mA

Operating Range

Device	Range	Ambient Temperature	V_{CC}
CY62147V18	Industrial	–40°C to +85°C	1.65V to 1.95V
CY62147V	Industrial	–40°C to +85°C	2.7V to 3.6V

Product Portfolio

Product	V_{CC} Range			Speed	Power Dissipation (Industrial)			
					Operating (I_{CC})		Standby (I_{SB2})	
	$V_{CC(min)}$	$V_{CC(typ)}$[2]	$V_{CC(max)}$		Typ.[2]	Maximum	Typ.[2]	Maximum
CY62147V	2.7V	3.0V	3.6V	70 ns	7 mA	15 mA	2 µA	20 µA
CY62147V18	1.65V	1.8V	1.95V	70 ns	3 mA	7 mA		15 µA

Shaded areas contain preliminary information.

Notes:

1. V_{IL}(min) = –2.0V for pulse durations less than 20 ns.
2. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC} Typ, T_A = 25°C.

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions			CY62147V			Unit
					Min.	Typ.[2]	Max.	
V_{OH}	Output HIGH Voltage	I_{OH} = –1.0 mA	V_{CC} = 2.7V		2.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 2.1 mA	V_{CC} = 2.7V				0.4	V
V_{IH}	Input HIGH Voltage		V_{CC} = 3.6V		2.2		V_{CC} + 0.5V	V
V_{IL}	Input LOW Voltage		V_{CC} = 2.7V		–0.5		0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}			–1	±1	+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled			–1	+1	+1	µA
I_{CC}	V_{CC} Operating Supply Current	I_{OUT} = 0 mA, f = f_{MAX} = 1/t_{RC}, CMOS Levels	V_{CC} = 3.6V			7	15	mA
		I_{OUT} = 0 mA, f = 1 MHz, CMOS Levels				1	2	mA
I_{SB1}	Automatic CE Power-Down Current—CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.3V, V_{IN} ≥ V_{CC} – 0.3V or V_{IN} ≤ 0.3V, f = f_{MAX}					100	µA
I_{SB2}	Automatic CE Power-Down Current—CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.3V V_{IN} ≥ V_{CC} – 0.3V or V_{IN} ≤ 0.3V, f = 0	V_{CC} = 3.6V	LL		2	20	µA

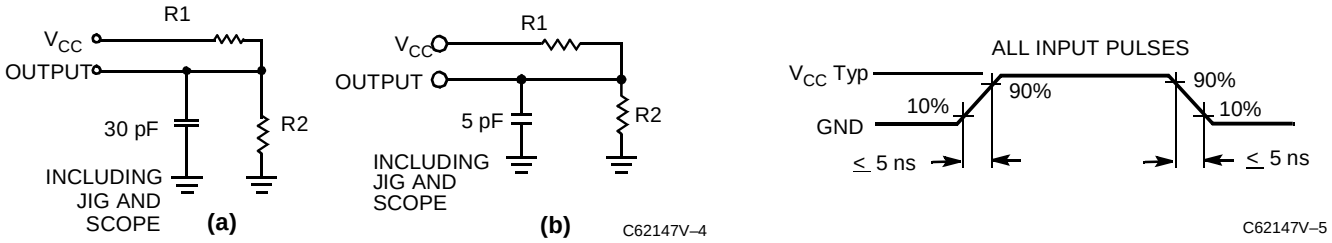
Parameter	Description	Test Conditions			CY62147V18			Unit
					Min.	Typ.[2]	Max.	
V_{OH}	Output HIGH Voltage	I_{OH} = –0.1 mA	V_{CC} = 1.65V		1.5			V
V_{OL}	Output LOW Voltage	I_{OL} = 0.1 mA	V_{CC} = 1.65V				0.2	V
V_{IH}	Input HIGH Voltage		V_{CC} = 1.95V		1.4		V_{CC} + 0.3V	V
V_{IL}	Input LOW Voltage		V_{CC} = 1.65V		–0.5		0.4	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}			–1	±1	+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled			–1	+1	+1	µA
I_{CC}	V_{CC} Operating Supply Current	I_{OUT} = 0 mA, f = f_{MAX} = 1/t_{RC}, CMOS Levels	V_{CC} = 1.95V			3	7	mA
		I_{OUT} = 0 mA, f = 1 MHz, CMOS Levels				1	2	mA
I_{SB1}	Automatic CE Power-Down Current—CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.3V, V_{IN} ≥ V_{CC} – 0.3V or V_{IN} ≤ 0.3V, f = f_{MAX}					100	µA
I_{SB2}	Automatic CE Power-Down Current—CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.3V V_{IN} ≥ V_{CC} – 0.3V or V_{IN} ≤ 0.3V, f = 0	V_{CC} = 1.95V	LL		2	15	µA

Capacitance[3]

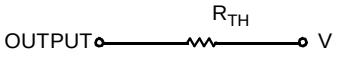
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	6	pF
C_{OUT}	Output Capacitance		8	pF

Notes:
3. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms



Equivalent to: THÉVENIN EQUIVALENT



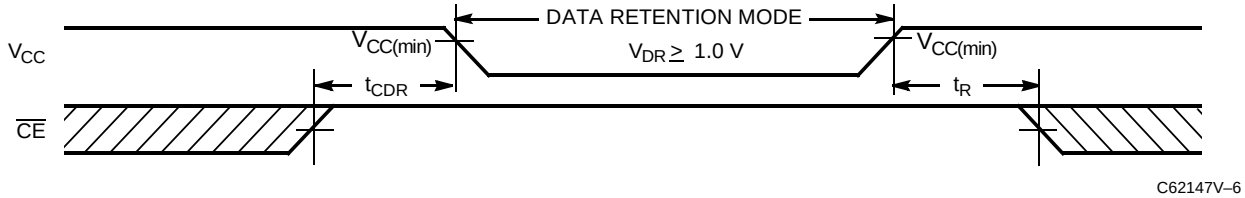
Parameters	3.0V	1.8V	Unit
R1	1105	15294	Ohms
R2	1550	11300	Ohms
R_{TH}	645	6500	Ohms
V_{TH}	1.75V	0.85V	Volts

Shaded areas contain preliminary information.

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions		Min.	Typ.[2]	Max.	Unit
V_{DR}	V_{CC} for Data Retention (CY62147V18)			1.0		1.95	V
V_{DR}	V_{CC} for Data Retention (CY62147V)			1.0		3.6	V
I_{CCDR}	Data Retention Current	V_{CC}= 1.0V $\overline{CE} \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$ No input may exceed V_{CC} + 0.3V	LL		0.2	5.5	µA
t_{CDR}[3]	Chip Deselect to Data Retention Time			0			ns
t_R	Operation Recovery Time			100			µs

Data Retention Waveform



Switching Characteristics Over the Operating Range[4]

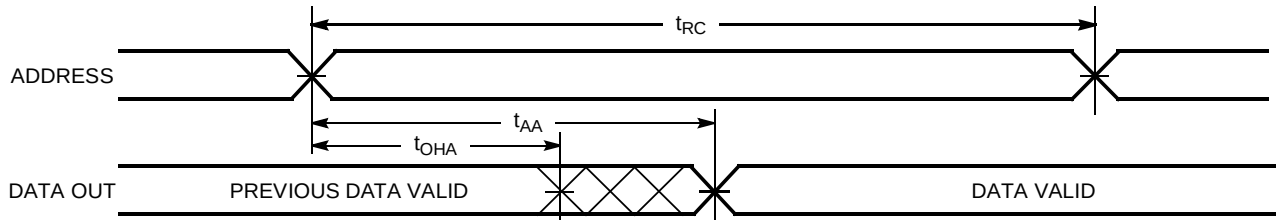
Parameter	Description	70 ns		Unit
		Min.	Max.	
READ CYCLE				
t_{RC}	Read Cycle Time	70		ns
t_{AA}	Address to Data Valid		70	ns
t_{OHA}	Data Hold from Address Change	10		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		70	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		35	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z[5, 6]	5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[6]		25	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[5]	10		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[5, 6]		25	ns
t_{PU}	$\overline{CE}$ LOW to Power-Up	0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-Down		70	ns
t_{DBE}	$\overline{BHE}$ / $\overline{BLE}$ LOW to Data Valid		70	ns
t_{LZBE}	$\overline{BHE}$ / $\overline{BLE}$ LOW to Low Z	5		ns
t_{HZBE}	$\overline{BHE}$ / $\overline{BLE}$ HIGH to High Z		25	ns
WRITE CYCLE[7, 8]				
t_{WC}	Write Cycle Time	70		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	60		ns
t_{AW}	Address Set-Up to Write End	60		ns
t_{HA}	Address Hold from Write End	0		ns
t_{SA}	Address Set-Up to Write Start	0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	50		ns
t_{BW}	$\overline{BHE}$ / $\overline{BLE}$ Pulse Width	60		ns
t_{SD}	Data Set-Up to Write End	30		ns
t_{HD}	Data Hold from Write End	0		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[5, 6]		25	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[5]	10		ns

Notes:

4. Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to V_{CC} typ., and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
5. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
6. t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with C_L = 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
7. The internal write time of the memory is defined by the overlap of $\overline{CE}$ LOW and $\overline{WE}$ LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
8. The minimum write cycle time for write cycle #3 ($\overline{WE}$ controlled, $\overline{OE}$ LOW) is the sum of t_{HZWE} and t_{SD}.

Switching Waveforms

Read Cycle No. 1[9, 10]



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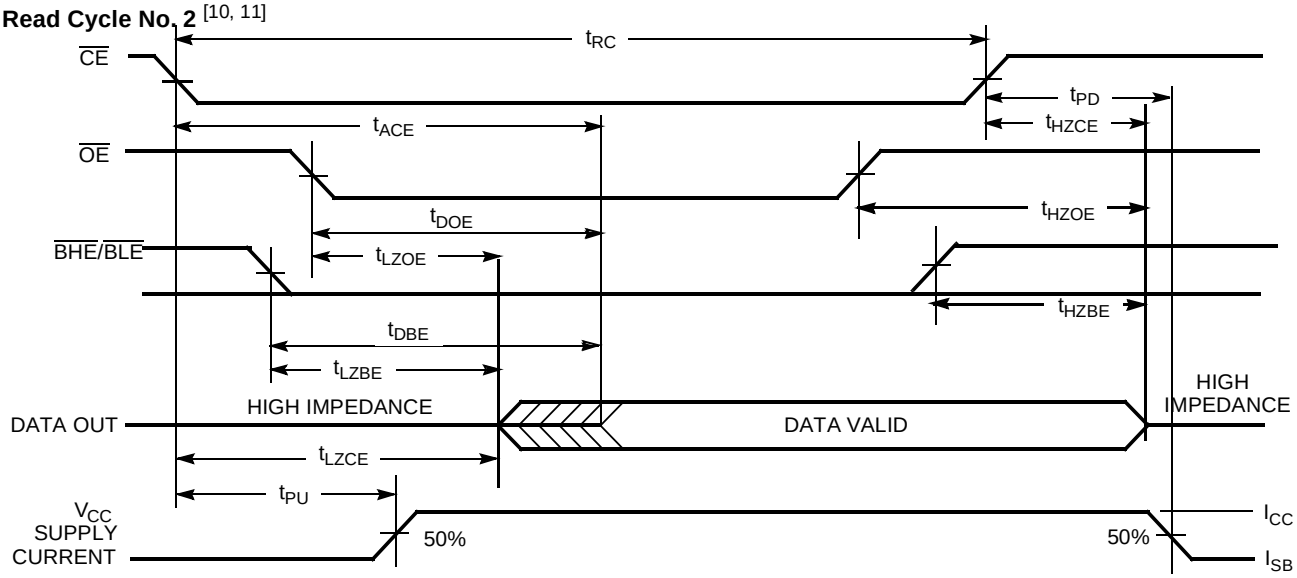
Read Cycle No. 2 [10, 11]

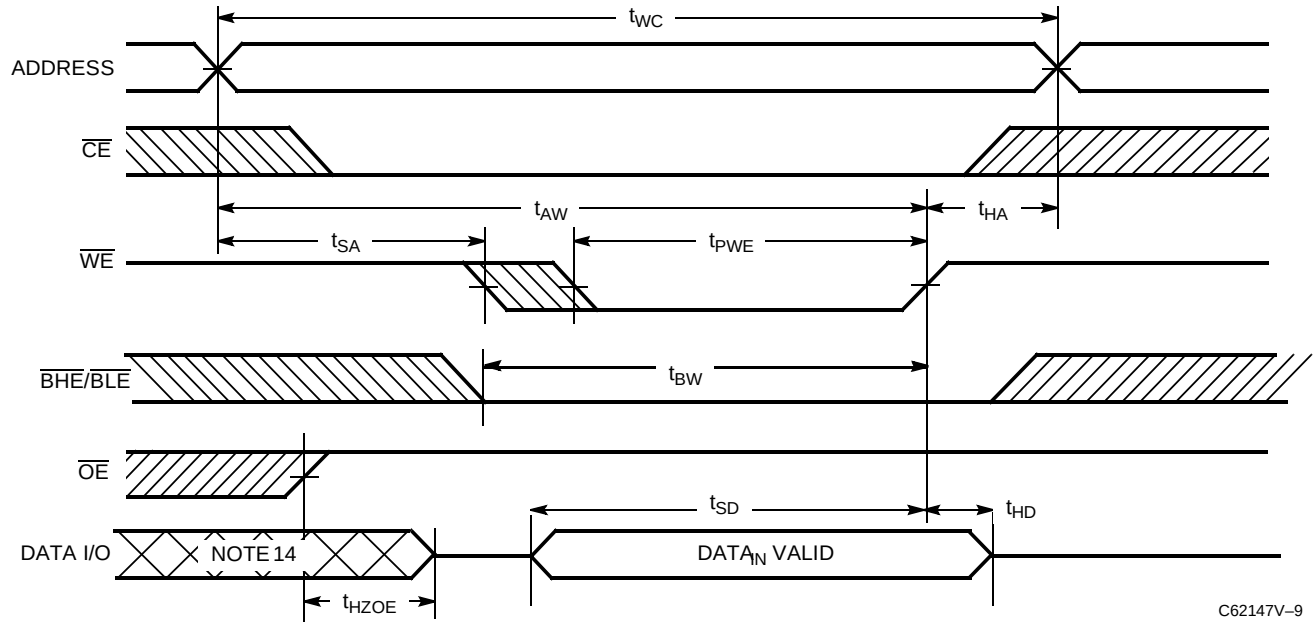


C62147V–8

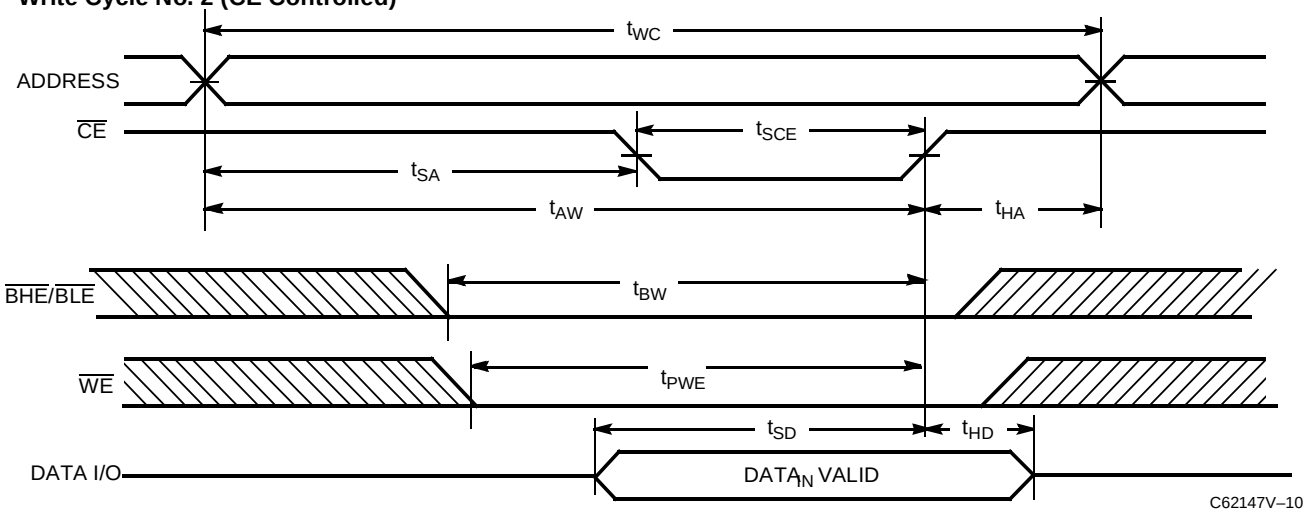
Notes:
9. Device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}.
10. $\overline{WE}$ is HIGH for read cycle.
11. Address valid prior to or coincident with $\overline{CE}$ transition LOW.

Switching Waveforms (continued)

Write Cycle No. 1 ($\overline{WE}$ Controlled) [7, 12, 13]



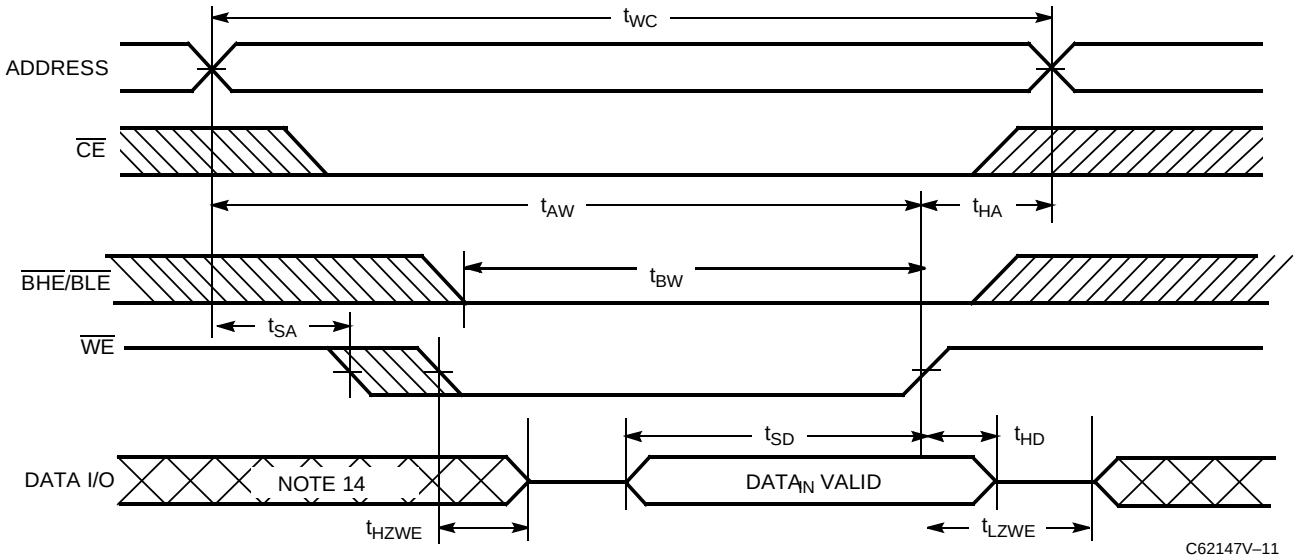
Write Cycle No. 2 ($\overline{CE}$ Controlled) [7, 12, 13]



Notes:
12. Data I/O is high-impedance if $\overline{OE} = V_{IH}$.
13. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ HIGH, the output remains in a high-impedance state.
14. During this period, the I/Os are in output state and input signals should not be applied.

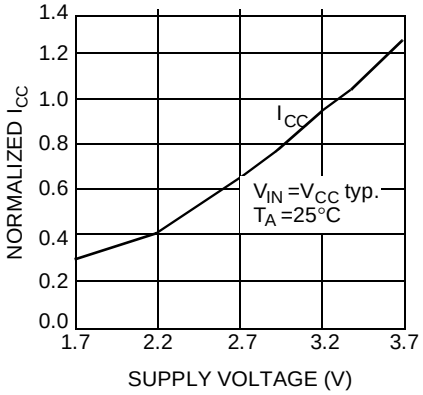
Switching Waveforms (continued)

Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)[8, 13]

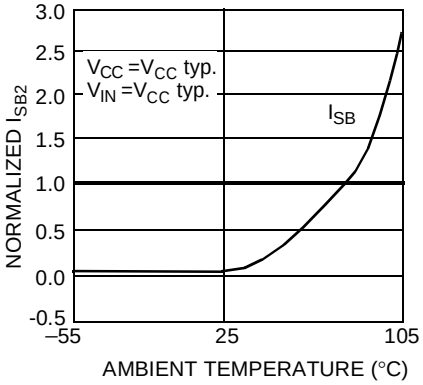


Typical DC and AC Characteristics

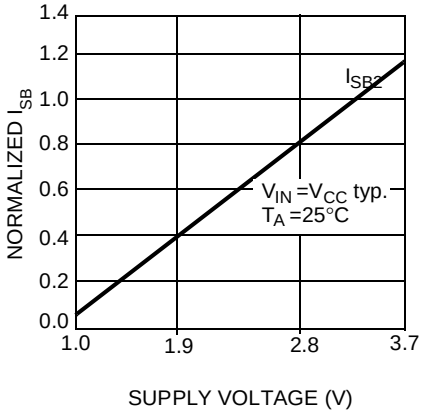
NORMALIZED SUPPLY CURRENT vs. SUPPLY VOLTAGE



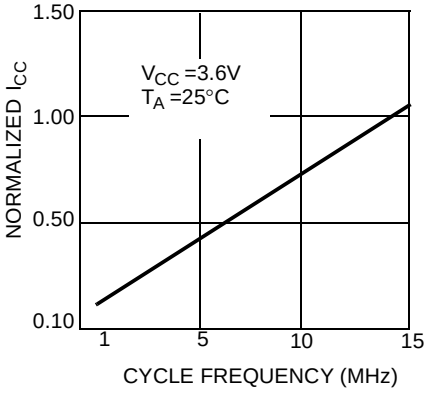
NORMALIZED STANDBY CURRENT vs. AMBIENT TEMPERATURE



NORMALIZED STANDBY CURRENT vs. SUPPLY VOLTAGE



NORMALIZED I_{CC} vs. CYCLE TIME



Truth Table

$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	High Z	Deselect/Power-Down	Standby (I_{SB})
L	X	X	H	H	High Z	Deselect/Power-Down	Standby (I_{SB})
L	H	L	L	L	Data Out (I/O_O–I/O_{15})	Read	Active (I_{CC})
L	H	L	H	L	Data Out (I/O_O–I/O_7); I/O_8–I/O_{15} in High Z	Read	Active (I_{CC})
L	H	L	L	H	Data Out (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Read	Active (I_{CC})
L	H	H	L	L	High Z	Deselect/Output Disabled	Active (I_{CC})
L	H	H	H	L	High Z	Deselect/Output Disabled	Active (I_{CC})
L	H	H	L	H	High Z	Deselect/Output Disabled	Active (I_{CC})
L	L	X	L	L	Data In (I/O_O–I/O_{15})	Write	Active (I_{CC})
L	L	X	H	L	Data In (I/O_O–I/O_7); I/O_8–I/O_{15} in High Z	Write	Active (I_{CC})
L	L	X	L	H	Data In (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Write	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
70	CY62147VLL-70ZI	Z44	44-Pin TSOP II	Industrial
	CY62147VLL-70BAI	BA49	48-Ball Fine Pitch BGA	
70	CY62147V18LL-70BAI	BA49	48-Ball Fine Pitch BGA	

Shaded areas contain preliminary information.

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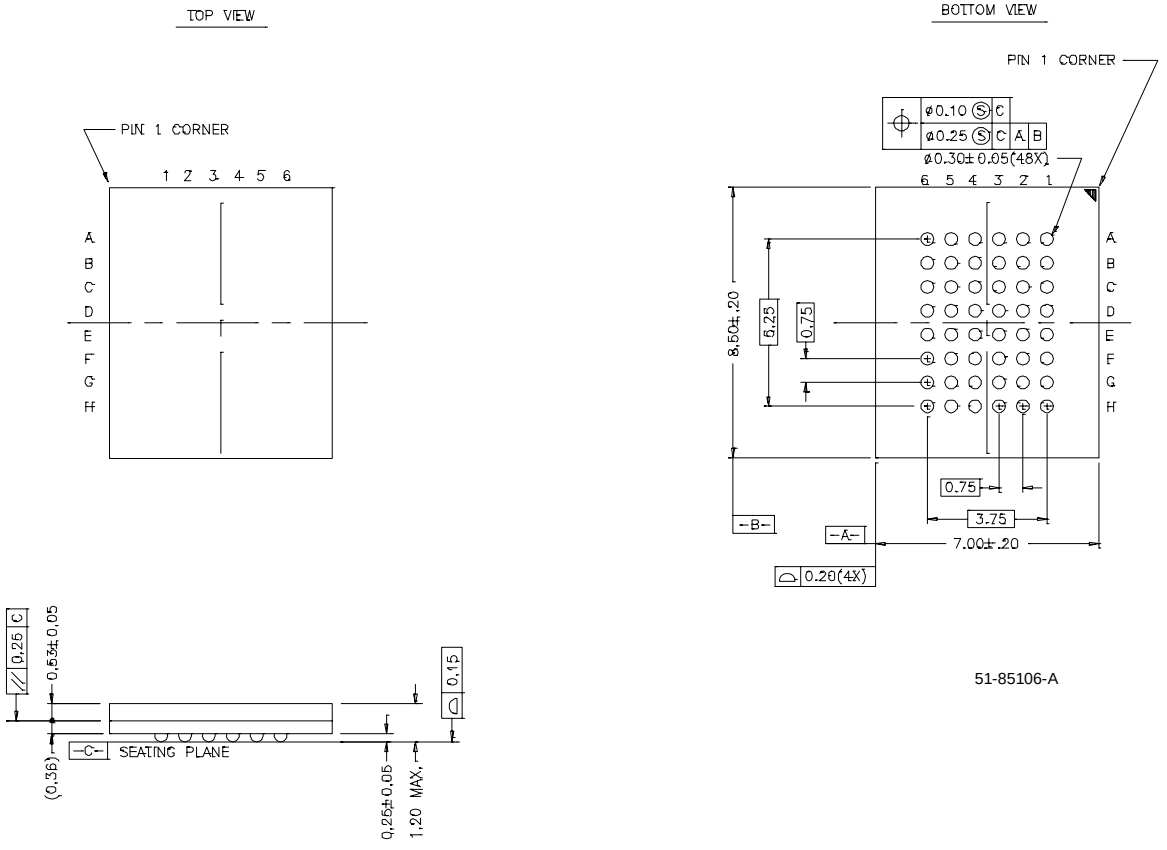
Package Diagrams

48-Ball (7.00 mm x 8.5 mm x 1.5 mm) FBGA BA49



* THE BALL DIAMETER, BALL PITCH, STAND-OFF & PACKAGE THICKNESS ARE DIFFERENT FROM JEDEC SPEC M0192 (LOW PROFILE BGA FAMILY)

Package Diagrams (continued)

44-Pin TSOP II Z44

DIMENSION IN MM (INCH)
MAX
MIN.